

SANYO Semiconductors

DATA SHEET



N-Channel Silicon MOSFET 2SK4064LS — General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- High reliability (Adoption of HVP process).
- Attachment workability is good by Mica-less package.
- · Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		600	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature	14	А
	I _{Dpack} *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	9.4	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	56	A
Allowable Power Dissipation	PD		2.0	W
		Tc=25°C (SANYO's ideal heat dissipation condition)*3	40	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		586	mJ
Avalanche Current *5	IAV		14	А

1 Shows chip capability

*2 Package limited

*3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

*4 VDD=99V, L=5mH, IAV=14A

*5 L≤5mH, single pulse

Marking: K4064

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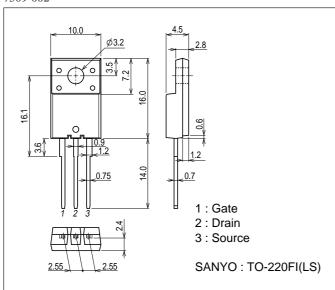
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Electrical Characteristics at Ta=25°C

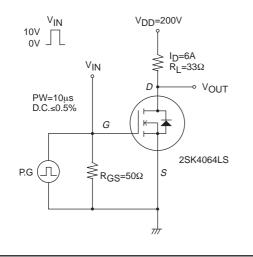
Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	600			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =600V, V _{GS} =0V			100	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	3		5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =6A	5	10		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	ID=6A, VGS=15V		0.45	0.58	Ω
Input Capacitance	Ciss	V _{DS} =30V, f=1MHz		2000		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		210		pF
Reverse Transfer Capacitance	Crss	V _{DS} =30V, f=1MHz		12		pF
		V _{DS} =5V, f=1MHz		25		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		52		ns
Rise Time	tr	See specified Test Circuit.		84		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		78		ns
Fall Time	tf	See specified Test Circuit.		58		ns
Total Gate Charge	Qg	V _{DS} =200V, V _{GS} =10V, I _D =12A		37		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =12A		14		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =200V, V _{GS} =10V, I _D =12A		12.5		nC
Diode Forward Voltage	VSD	IS=12A, VGS=0V		0.9	1.2	V

Package Dimensions

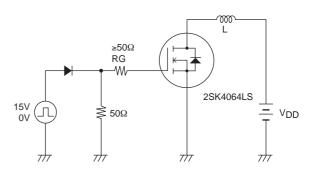
unit : mm (typ) 7509-002



Switching Time Test Circuit

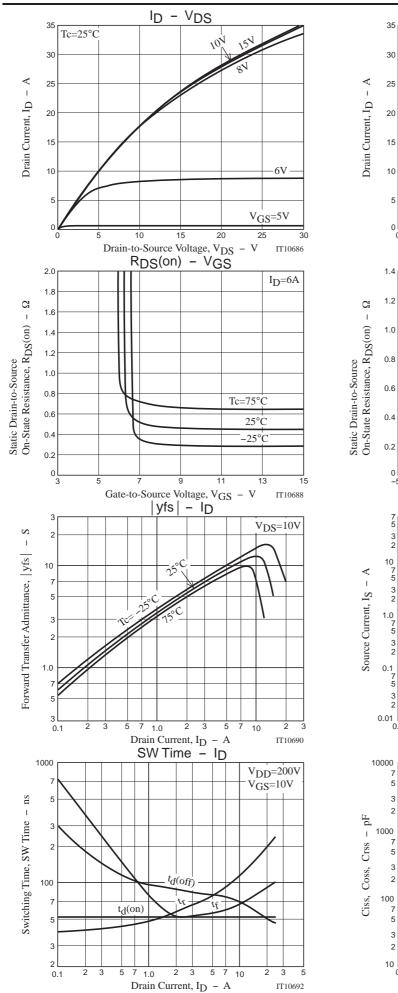


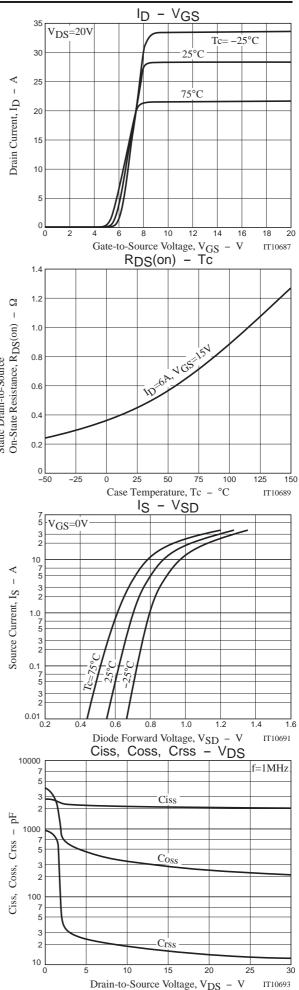
Avalanche Resistance Test Circuit



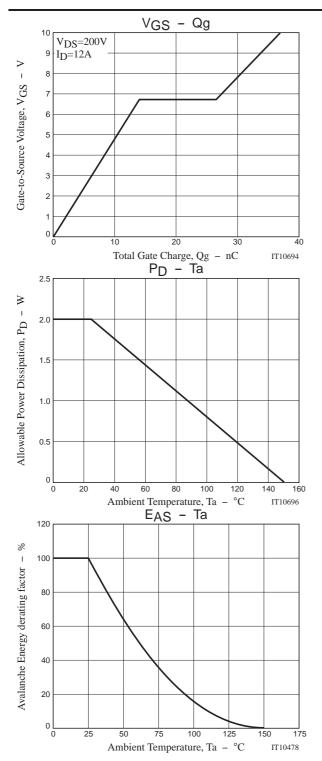
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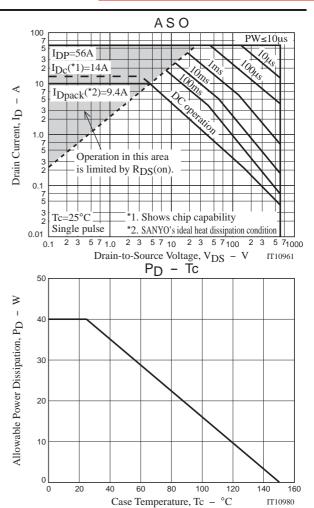
2SK4064LS





2SK4064LS





Note on usage : Since the 2SK4064LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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